

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
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**INFORMATION DISCLOSURE
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(Use several sheets if necessary)

APPLICANTS

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FILING DATE

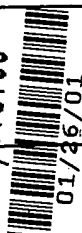
January 26, 2001

GROUP ART UNIT

Unassigned

jc944 U.S. PTO

09/770788



U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

dhru			<u>A Novel-Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories</u>
			by Farid Nemati and James D. Plummer, Center for Integrated Systems, Stanford, University, 1999
dhru			<u>A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device</u> , by Farid Nemati and
			James D. Plummer, Center for Integrated Systems, Stanford University, 1998

EXAMINER

DATE CONSIDERED

11/19/2001

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.